Silicon NPN Power Transistors 2SC3322

DESCRIPTION

- With TO-3P(I) package
- High voltage
- High speed

APPLICATIONS

- High power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

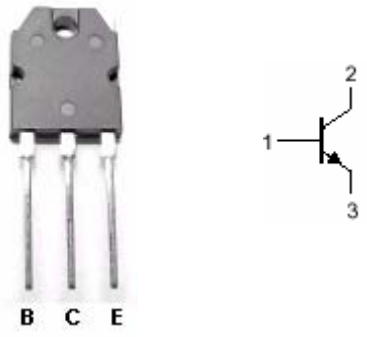

Fig.1 simplified outline (TO-3P(I)) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		5	A
I_{CM}	Collector current-peak		10	A
I_B	Base current		2.5	A
P_T	Total power dissipation	T_C=25℃	80	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.2A ,L=100mH;R_{BE}=∞	800			V
$V_{(BR)EBO}$	Base-emitter breakdown voltage	I_E=10mA; I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1.5A; I_B=0.3A			1.0	V
$V_{BE\ sat}$	Base-emitter saturation voltage	I_C=1.5A; I_B=0.3A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=750V; I_E=0			100	μA
I_{CEO}	Collector cut-off current	V_{CE}=650V; R_{BE}=∞			100	μA
h_{FE-1}	DC current gain	I_C=0.5A ; V_{CE}=5V	15			
h_{FE-2}	DC current gain	I_C=3A ; V_{CE}=5V	7			
Switching times						
t_{on}	Turn-on time	I_C=3A ; V_{CC}≈250V I_{B1}=0.6A; I_{B2}=-1.5A			1.0	μs
t_{stg}	Storage time				3.0	μs
t_f	Fall time				1.0	μs

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PACKAGE OUTLINE

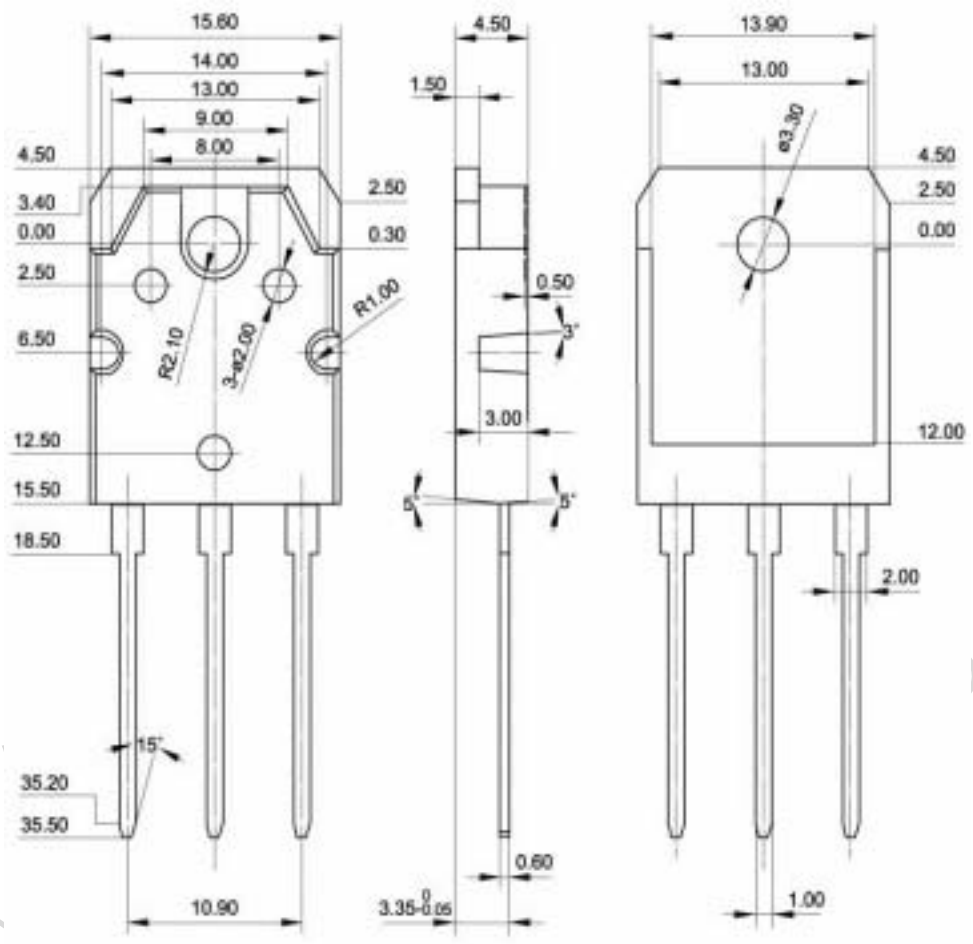

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)